



## REPLACEMENT TEXT

Following are "clean" replacement paragraphs in accordance with amendments herein:

**Replacement text for paragraph beginning at page 26, line 13 and spanning to page 27, line 22:**

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With reference to Fig. 8, the semiconductor switch according to the present invention comprises two cathode electrodes 8, and the anode electrode 7 which are enclosed by an active layer 3. From two cathode electrodes 8, one together with the anode electrode 7 form a Schottky barrier diode. In addition, the other cathode electrode 8, likewise, together with the anode electrode 7 may be considered to form a Schottky barrier diode, or may be considered to be an additional electrode established as an annex to the Schottky barrier diode. Anyway, the two cathode electrodes 8 are both connected to the earth, and are disposed in parallel to each other in a predetermined direction on the semiconductor substrate (in this example, in the right-left lateral direction on the paper surface). In addition, the anode electrode 7 is disposed so as to be sandwiched between the two cathode electrodes 8 as well as, likewise, to be in parallel to each other in a predetermined direction on the semiconductor substrate. The anode electrode 7 has undergone Schottky junction with semiconductor crystal, and the cathode electrodes 8 have undergone ohmic junction with semiconductor crystal. In detail, referring to Fig. 8B, an i-AlGaAs layer is formed on an i-GaAs layer. An i-InGaAs layer as a channel layer is formed on the i-AlGaAs layer. A n-AlGaAs layer is formed on the i-InGaAs layer. The cathode electrodes 8 are formed on the n-AlGaAs layer apart from each other through the respective n<sup>+</sup>-GaAs layer. The anode electrode 7 is formed on the n-AlGaAs

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layer. The anode electrode 7 is made by aluminum, gold, molybdenum, titanium or tungsten silicide. The cathode electrodes 8 are made by an alloy including AuGe or nickel. Both the ends of the anode electrode 7 in the predetermined direction operate respectively as the first input-output unit and the second input-output unit, and are respectively connected with the first input-output terminal 1 and the second input-output terminal 2. Such semiconductor switches are driven by supplying the anode electrode 7 with positive voltage as well as zero bias outside the active layer 3 by a not-shown bias line via a resistance.

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